



Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

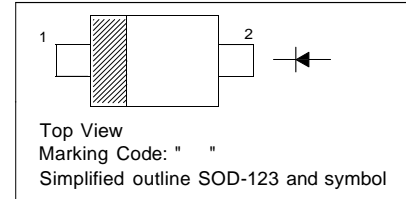
MARKING: B0520LW:SD

B0530W: SE

B0540W: SF

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Maximum Ratings @Ta=25°C

Parameter	Symbol	B0520LW	B0530W	B0540W	Unit
Peak repetitive peak reverse voltage					
Working peak reverse voltage	V_{RRM}				
DC Blocking voltage	V_{RWM} V_R	20	30	40	V
RMS reverse voltage reverse voltage (DC)	$V_{R(RMS)}$	14	20	28	V
Average rectified output current	I_o		0.5		A
Forward surge current peak	I_{FSM}		5.5		A
Power dissipation	P_D		500		mW
Thermal resistance junction to ambient	$R_{\theta JA}$		250		°C/W
Junction temperature	T_j		150		°C
Storage temperature	T_{STG}		-55~+150		°C
Voltage rate of change	dv/dt		1000		V/μS

Electrical Characteristics @Ta=25°C

Parameter	Symbol	B0520LW	B0530W	B0540W	Unit	Conditions
Minimum reverse breakdown voltage	$V_{(BR)R}$	20	--	--	V	$I_R=250 \mu A$
		--	30	--		$I_R=200 \mu A$
		--	--	40		$I_R=20 \mu A$
Forward voltage	V_{F1}	0.32	0.375	--	V	$I_F=0.1A$
	V_{F2}	0.385	0.430	0.510		$I_F=0.5A$
	V_{F3}	--	--	0.62		$I_F=1A$
Reverse current	I_{R1}	75	--	--	μA	$V_R=10V$
	I_{R2}	--	20	--		$V_R=15V$
Reverse current	I_{R3}	250	--	10	μA	$V_R=20V$
	I_{R4}	--	130	--		$V_R=30V$
	I_{R5}	--	--	20		$V_R=40V$
Capacitance between terminals	C_T	--	--	170	pF	$V_R=0, f=1MHz$



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B0520LW/B0530W/B0540W

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